SMD Schottky Barrier Diode

COMCHIP
SMD DIODE SPECIALIST

CDBG820-G THRU CDBG860-G (RoHS Device)

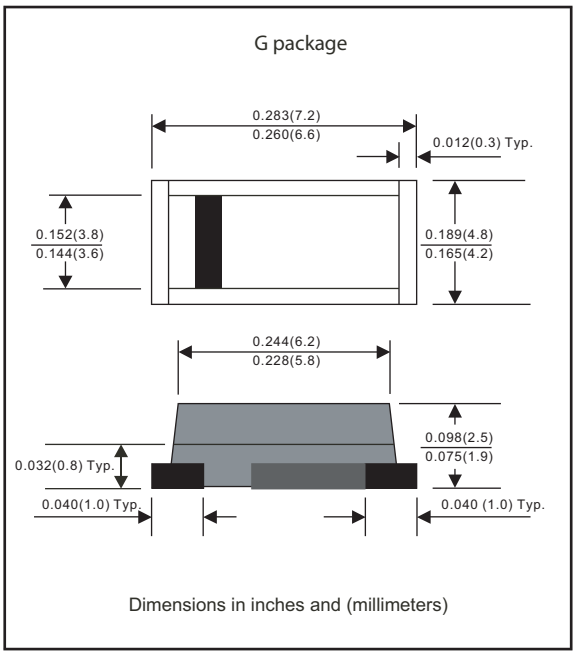
Reverse Voltage: 20 ~ 60 Volts
Forward Current: 8 A

Features:

- Plastic package has Underwriters Laboratory Flammability Classification 94V-O Utilizing Flame Retardant Epoxy Molding Compound.
- For surface mounted applications.
- Exceeds enviromental standards of MIL-S-19500/228
- Low leakage current

Mechanical Data:

- Case: Molded plastic, G package (6.9mmx4.5mm)
- Terminals: Solder plated, solderable per MIL-STD-750, method 2026.
- Polarity: Indicated by cathode band
- Mounting position: Any
- Approx. Weight: 0.00585 ounce, 0.195 gram



Maximum Ratings (at T_A = 25°C unless otherwise noted)

Parameter	Symbol	CDBG820-G	CDBG830-G	CDBG840-G	CDBG850-G	CDBG860-G	Unit
Marking Code		SS82	SS83	SS84	SS85	SS86	
Repetitive Peak Reverse Voltage	V_{RRM}	20	30	40	50	60	V
RMS voltage	V_{RMS}	14	21	28	35	42	V
Continuous reverse voltage	V_R	20	30	40	50	60	V
Maximum forward voltage	V_F	0.55			0.70		V
Max. Forward rectified current (See Fig.1)	I_O	8.0					A
Max. Forward surge current 8.3ms single half sine-wave superimposed on rate load (JEDEC method)	I_{FSM}	150					A
Max. Reverse current $V_R = V_{RRM}$ T_A = 25°C	I_R	1.0					mA
$V_R = V_{RRM}$ T_A = 100°C		50					
Thermal resistance Junction Ambient	R_{JA}	55					°C/ W
Diode junction capacitance f=1MHz and applied 4vDC reverse Voltage	C_j	700					pF
Max. Storage temperature	T_{STG}	+150					°C
Operating temperature		-55 to +125					°C

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RATING AND CHARACTERISTIC CURVES (CDBG820-G THRU CDBG860-G)

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

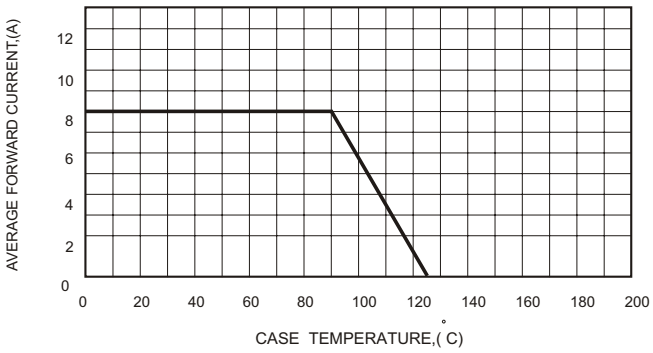

FIG.2-TYPICAL FORWARD CHARACTERISTICS

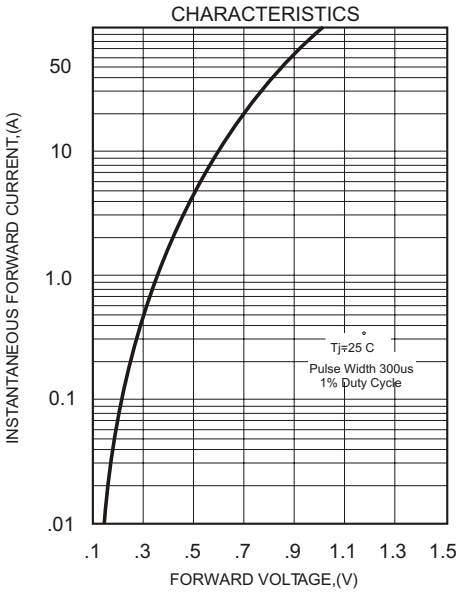

FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

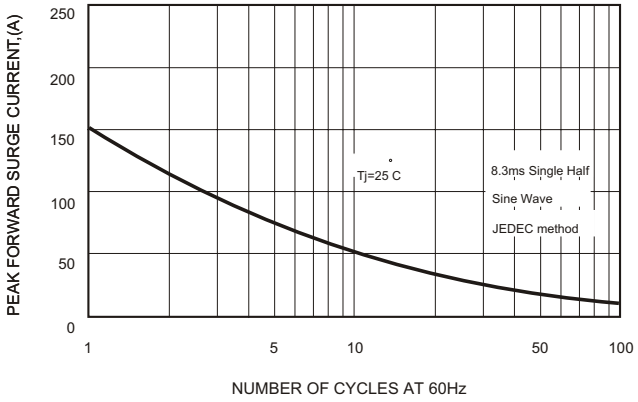

FIG.4-TYPICAL JUNCTION CAPACITANCE

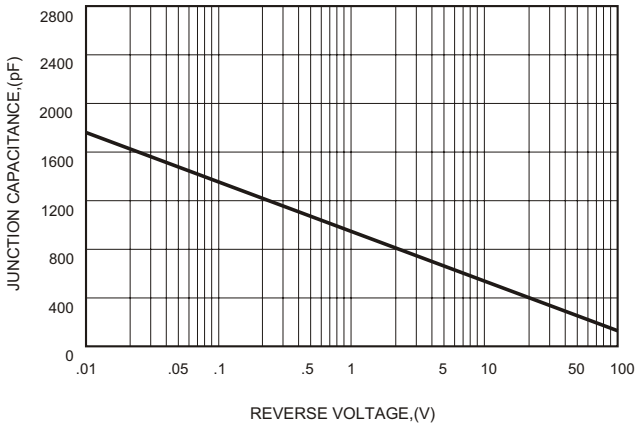

FIG.5 - TYPICAL REVERSE CHARACTERISTICS